1. Record Nr. UNINA9910817124503321 Autore Voldman Steven H Titolo ESD: failure mechanisms and models // Steven H. Voldman Pubbl/distr/stampa Chichester, West Sussex, U.K.; Hoboken, NJ,: J. Wiley, 2009 **ISBN** 1-282-23713-6 9786612237133 0-470-74725-0 0-470-74726-9 Edizione [1st ed.] Descrizione fisica 1 online resource (410 p.) 621.381 Disciplina Soggetti Semiconductors - Failures Integrated circuits - Protection Integrated circuits - Testing Integrated circuits - Reliability Electric discharges **Electrostatics** Lingua di pubblicazione Inglese **Formato** Materiale a stampa Livello bibliografico Monografia Description based upon print version of record. Note generali Nota di bibliografia Includes bibliographical references and index. Nota di contenuto ESD Failure Mechanisms and Models; Contents; About the Author; Preface; Acknowledgments; 1 Failure Analysis and ESD; 1.1 INTRODUCTION: 1.1.1 FA Techniques for Evaluation of ESD Events: 1.1.2 Fundamental Concepts of ESD FA Methods and Practices; 1.1.3 ESD Failure: Why Do Semiconductor Chips Fail?: 1.1.4 How to Use FA to Design ESD Robust Technologies; 1.1.5 How to Use FA to Design ESD Robust Circuits; 1.1.6 How to Use FA for Temperature Prediction; 1.1.7 How to Use Failure Models for Power Prediction; 1.1.8 FA Methods, Design Rules, and ESD Ground Rules 1.1.9 FA and Semiconductor Process-Induced ESD Design Asymmetry 1.1.10 FA Methodology and Electro-thermal Simulation; 1.1.11 FA and ESD Testing Methodology; 1.1.12 FA Methodology for Evaluation of ESD

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Sommario/riassunto

Electrostatic discharge (ESD) failure mechanisms continue to impact semiconductor components and systems as technologies scale from micro- to nano-electronics. This book studies electrical overstress, ESD, and latchup from a failure analysis and case-study approach. It provides a clear insight into the physics of failure from a generalist perspective, followed by investigation of failure mechanisms in specific technologies, circuits, and systems. The book is unique in covering both the failure mechanism and the practical solutions to fix the problem from either a technology or circuit method

3.2 LOCOS ISOLATION-DEFINED CMOS

Failure Mechanisms: 3.1 TABLES OF CMOS ESD FAILURE MECHANISMS